L Number	Hits 909		DB HEDAT	Time stamp	00.27
-	909	((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and	USPAT; US-PGPUB;	2003/03/27	09:37
		(methor process)	EPO; JPO;		
	1		DERWENT		
-	468	(((mold near2 (upper lower)) and	USPAT;	2002/09/20	09:57
		semiconductor and (chip die wafer)) and	US-PGPUB;		
		(methor process)) and (inject injecting	EPO; JPO;		
_	403	injected) ((((mold near2 (upper lower)) and	DERWENT USPAT;	2002/09/20	00.50
_	1 403	semiconductor and (chip die wafer)) and	US-PGPUB;	2002/03/20	09.50
		(methor process)) and (inject injecting	EPO; JPO;		
		injected)) and (resin encapsulant sealing)	DERWENT		
-	1	(((((mold near2 (upper lower)) and	USPAT;	2002/09/20	10:08
		semiconductor and (chip die wafer)) and (methor process)) and (inject injecting	US-PGPUB; EPO; JPO;		
	1	injected)) and (resin encapsulant	DERWENT		
	1	sealing)) and ((releasable released			
		releasing) near1 (layer film material))		}	
-	101	(((((mold near2 (upper lower)) and	USPAT;	2002/09/20	10:03
	1	semiconductor and (chip die wafer)) and	US-PGPUB;		
		(methor process)) and (inject injecting injected)) and (resin encapsulant	EPO; JPO; DERWENT		
		sealing)) and (releasable released	DERWENT		
	i	releasing)	1		
-	63	((((((mold near2 (upper lower)) and	USPAT;	2003/03/27	11:06
	i	semiconductor and (chip die wafer)) and	US-PGPUB;		
		(methor process)) and (inject injecting injected)) and (resin encapsulant	EPO; JPO; DERWENT		
		sealing)) and (releasable released	DERWENT		
	ļ	releasing)) and ((flipchip (flip adj			
		chip)) bump ball)			
-	179	(mold near2 (upper lower)) and	USPAT;	2002/09/20	10:10
	ı	((releasable released releasing) nearl	US-PGPUB;		
1	i	(layer film material))	EPO; JPO; DERWENT		
_	12	((mold near2 (upper lower)) and	USPAT;	2002/09/20	10.27
		((releasable released releasing) near1	US-PGPUB;	2002/03/20	10.2.
	ı	(layer film material))) and semiconductor	EPO; JPO;		
		and (chip die wafer)	DERWENT		
-	0 5	6123895.URPN. ("3178807" "5006417" "5384087"	USPAT	2002/09/20	
-	1	"5616421" "5902943").PN.	USPAT	2002/09/20	10:10
-	1	jp408142106a	USPAT;	2002/09/20	10:29
		,,	US-PGPUB;		
			EPO; JPO;		
	1.56	Maria atau	DERWENT	0000/00/00	
-	126	MIYAJIMA-FUMIO	USPAT; US-PGPUB;	2002/09/20	10:30
ſ	ı		EPO; JPO;		
1			DERWENT		
- 1	19	MIYAJIMA-FUMIO	USPAT; EPO	2002/09/20	
-	1	6187243.pn. and (parting adj face)	USPAT;	2002/09/20	14:01
	1		US-PGPUB;		
- 1			EPO; JPO; DERWENT		
- 1	1481	(mold near2 (upper lower)) and	USPAT;	2003/05/08	09:42
ĺ		semiconductor and (chip die wafer)	US-PGPUB;		
ļ			EPO; JPO;		
J	39173	mald near? (unner lever)	DERWENT	2003/03/27	00.31
-	391/3	mold near2 (upper lower)	USPAT; US-PGPUB;	2003/03/27	09:34
1			EPO; JPO;		
1			DERWENT		
_	54	(mold near2 (upper lower)) near3 (air adj	USPAT;	2002/09/24	14:59
-	54	(mold near2 (upper lower)) near3 (air adj vent)	US-PGPUB;	2002/09/24	14:59
-	54	(mold near2 (upper lower)) near3 (air adj vent)	US-PGPUB; EPO; JPO;	2002/09/24	14:59
-		vent)	US-PGPUB; EPO; JPO; DERWENT		
-	5 4 8	vent) ((mold near2 (upper lower)) near3 (air adj	US-PGPUB; EPO; JPO; DERWENT USPAT;	2002/09/24	
-		vent)	US-PGPUB; EPO; JPO; DERWENT		

-	5628	tab near3 lead	USPAT; US-PGPUB;	2002/09/24 15:18
1			EPO; JPO;	
1	I		DERWENT	
-	1951	(tab near3 lead) and semiconductor and	USPAT;	2003/05/19 08:33
	l	(chip die wafer)	US-PGPUB;	
1			EPO; JPO;	
	92	((tab near3 lead) and semiconductor and	DERWENT	2002/05/20 00.24
1 -	92	((tab hears lead) and semiconductor and (chip die wafer)) and ((lead near3 (plated	USPAT; US-PGPUB;	2003/05/19 08:34
	1	plating electroplated electroplating))	EPO; JPO;	
		with (electrode terminal pad))	DERWENT	Α.
-	21		USPAT;	2002/09/24 15:29
	1	(chip die wafer)) and ((lead near3 (plated	US-PGPUB;	
]	plating electroplated electroplating))	EPO; JPO;	
	[with ((electrode terminal pad) near3 (chip	DERWENT	
	3900	die ic))) 257/787		2002/00/10 15
1	3900	431/101	USPAT; US-PGPUB;	2003/02/12 12:29
	1		EPO; JPO;	
	1		DERWENT	1
-	1339	257/787 and shape	USPAT;	2003/02/12 12:29
		•	US-PGPUB;	
1 1	l .		EPO; JPO;	
1		(057/707 -) -) -) -)	DERWENT	
-	57	(257/787 and shape) and leadless	USPAT;	2003/02/12 12:29
1 1	1		US-PGPUB;]
1			EPO; JPO; DERWENT	
-	40537	mold near2 (upper lower)	USPAT:	2003/05/08 09:40
1		\-rp	US-PGPUB;	1
			EPO; JPO;	
		l	DERWENT	
-	7365	(mold near2 (upper lower)) and (chip die wafer)	USPAT;	2003/03/27 09:37
1		warer)	US-PGPUB; EPO; JPO;	
			DERWENT	
-	4354	((mold near2 (upper lower)) and (chip die	USPAT;	2003/03/27 09:39
		wafer)) and (methor process)	US-PGPUB;	
			EPO; JPO;	
1			DERWENT	
-	5701	((mold near2 (upper lower)) and (chip die	USPAT;	2003/03/27 09:39
1 1		wafer)) and (method process)	US-PGPUB; EPO; JPO;	1
			DERWENT	
1-	173	(((mold near2 (upper lower)) and (chip	USPAT;	2003/03/27 09:45
		die wafer)) and (method process)) and	US-PGPUB;	
		(flipchip (flip adj chip))	EPO; JPO;	
	_		DERWENT	
-	0	((((mold near2 (upper lower)) and (chip	USPAT;	2003/03/27 11:07
1		die wafer)) and (method process)) and (flipchip (flip adj chip))) and	US-PGPUB; EPO; JPO;	
		((releasable released releasing) near	DERWENT	
		(film layer tape))	DERWEINT	
-	12	((((mold near2 (upper lower)) and (chip	USPAT;	2003/03/27 14:36
1	- 1	dic wafer)) and (method process)) and	US-PGPUB;	1
		(flipchip (flip adj chip))) and	EPO; JPO;	
		((releasable released release releasing)	DERWENT	
	0	near (film layer tape)) 20020017738.URPN.	UODAM	2002/02/27 12 22
	55	((((mold near2 (upper lower)) and (chip	USPAT;	2003/03/27 12:20
	33	die wafer)) and (method process)) and	US-PGPUB;	2003/03/2/ 14:33
1		(flipchip (flip adj chip))) and	EPO; JPO;	
		(releasable released release releasing)	DERWENT	

<u> </u>	43	(((((mold near2 (upper lower)) and (chip	USPAT;	2003/03/27 12:24
	1	die wafer)) and (method process)) and	US-PGPUB;	1
	1	(flipchip (flip adj chip))) and	EPO; JPO;	1
	1	(releasable released release releasing))	DERWENT	1
		not (((((mold near2 (upper lower)) and (chip die wafer)) and (method process))		
	l .	and (flipchip (flip adj chip))) and	1	1
		((releasable released release releasing)		1
	ŀ	near (film layer tape)))		1 1
_	98	5450283.URPN.	USPAT	2003/03/27 14:35
-	759	(((mold near2 (upper lower)) and (chip	USPAT	2003/03/27 14:35
	1	die wafer)) and (method process)) and		
		(bump ball)		
-	671	((((mold near2 (upper lower)) and (chip	USPAT	2003/03/27 14:35
		die wafer)) and (method process)) and		1
	1	(bump ball)) not (((mold near2 (upper		1 1
		lower)) and (chip die wafer)) and (method		
		process)) and (flipchip (flip adj chip)))		
-	275	(((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and	USPAT;	2003/03/27 14:36
		die wafer)) and (method process)) and	US-PGPUB;	1
1	1	(bump ball)) not ((((mold near2 (upper	EPO; JPO;	1 1
	i	lower)) and (chip die wafer)) and (method	DERWENT	
	1	process)) and (flipchip (flip adj chip))))		
	1	and (releasable released release		1
	10	releasing)		0000100100
	1 10	(((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and	USPAT;	2003/03/27 14:43
		(bump ball)) not ((((mold near2 (upper	US-PGPUB; EPO; JPO;	1
1	1	lower)) and (chip die wafer)) and (method	DERWENT	1 1
	1	process)) and (flipchip (flip adj chip))))	DERWENT	1
	1	and ((releasable released release	}	1
		releasing) nearl (film layer tape))	ļ	1
_	2	6019588.URPN.	USPAT	2003/03/27 14:41
_	16	("4044984" "4236689" "4332537"	USPAT	2003/03/27 14:41
		"4442056" "4470786" "4697784"		2000,00,2. 11111
		"4779835" "5059105" "5118271"	1	1
	1	"5218759" "5429488" "5484274"		
		"5626886" "5639695" "5693572"	1	1
10		"5779958").PN.		
-	265	((((((mold near2 (upper lower)) and (chip	USPAT;	2003/03/27 14:43
		die wafer)) and (method process)) and	US-PGPUB;	
		(bump ball)) not (((mold near2 (upper	EPO; JPO;	1 1
		lower)) and (chip die wafer)) and (method	DERWENT	
	1	process)) and (flipchip (flip adj chip))))		1
	Ì	and (releasable released release	1	1
		releasing)) not (((((mold near2 (upper	l	
	1	lower)) and (chip die wafer)) and (method		1
		process)) and (bump ball)) not (((mold		
	1	near2 (upper lower)) and (chip die	1	
		wafer)) and (method process)) and (flipchip (flip adj chip)))) and		
	I	((releasable released release releasing)	[1
		nearl (film layer tape)))	1	1
_	1	"20030052418"	USPAT;	2003/05/08 09:32
	,	2000002110	US-PGPUB;	2003/03/00 09:32
	1		EPO; JPO;	
	l .		DERWENT	
_	40999	mold near2 (upper lower)	USPAT;	2003/05/08 09:41
	1		US-PGPUB;	,,
			EPO; JPO;]
			DERWENT	
-	1694	(mold near2 (upper lower)) and	USPAT;	2003/05/08 09:42
		semiconductor and (chip die wafer)	US-PGPUB;	
			EPO; JPO;	1 1
			DERWENT	1 1
_	446		DERWENT USPAT;	2003/05/08 09:45
-	446	semiconductor and (chip die wafer)) and		2003/05/08 09:45
-	446		USPAT;	2003/05/08 09:45

-	395	(((mold near2 (upper lower)) and	USPAT;	2003/05/08 12:18
		semiconductor and (chip die wafer)) and	US-PGPUB;	Į.
		(leadframe (lead near1 (inner outer))))	EPO; JPO;	1
		and (sealing sealed encapsulant	DERWENT	1
1_	369	encapsulating encapsulated) ((((mold near2 (upper lower)) and	US PAT;	2003/05/08 09:47
1	303	semiconductor and (chip die wafer)) and	US-PGPUB;	2003/03/08 09:47
1		(leadframe (lead near1 (inner outer))))	EPO; JPO;	l .
1		and (sealing sealed encapsulant	DERWENT	ľ
		encapsulating encapsulated)) and (method		i
		process)		
-	122	(((((mold near2 (upper lower)) and	USPAT;	2003/05/08 09:47
1		semiconductor and (chip die wafer)) and	US-PGPUB;	
		(leadframe (lead nearl (inner outer))))	EPO; JPO;	
		and (sealing sealed encapsulant	DERWENT	
1		encapsulating encapsulated)) and (method		l .
1_	53	process)) and ((die mounting) adj pad)	USPAT	2003/05/08 09:52
1 -	. 0	6472252.URPN.	USPAT	2003/05/08 09:59
l -	36	("4313718" "4697784" "4881884"	USPAT	2003/05/08 09:59
1		"4944908" "5147821" "5355283"		
		"5362679" "5405255" "5406699"		
		"5467253" "5468999" "5474958"	1	1
		"5477611" "5479051" "5490324"		
		"5506756" "5508565" "5527743"	1	1
		"5543658" "5545922" "5556807"		
		"5596227" "5609889" "5626886" "5656549" "5663106" "5665281"	Ĭ)
		"5688716" "5766649" "5766650"	i .	
		"5817545" "5876765" "5923959"	1	
		"5928595" "6117382" "6281588").PN.		ll .
-	3	6117382.URPN.	USPAT	2003/05/08 10:01
1- !	20	("5034350" "5114880" "5147815"	USPAT	2003/05/08 10:02
		"5222014" "5239806" "5313365"		
1 1		"5331205" "5366364" "5458694"		1
		"5488257" "5578261" "5597643"		
1		"5598034" "5608262" "5609889"		
1 1		"5614441" "5615089" "5646829"		1
1 1	20	"5755914" "5830781").PN.	rio Dam	2003/05/00 10:04
1- 1	20	("5034350" "5114880" "5147815" "5222014" "5239806" "5313365"	USPAT	2003/05/08 10:04
1		"5331205" "5366364" "5458694"	1	1
		"5488257" "5578261" "5597643"		
1)		"5598034" "5608262" "5609889"	ì	1
!		"5614441" "5615089" "5646829"		l
1 1		"5755914" "5830781").PN.		
[- [5923959.URPN.	USPAT	2003/05/08 10:05
-	20	("5355283" "5362679" "5406699"	USPAT	2003/05/08 10:10
		"5467253" "5468999" "5474958"	1	
		"5477611" "5479051" "5490324"	1	
1		"5506756" "5508565" "5527743" "5543658" "5545922" "5556807"	1	
		"5596227" "5609889" "5656549"		
1		"5596227" "5609889" "5656549" "5663106" "5688716").PN.	1	
1- 1	21	5609889.URPN.	USPAT	2003/05/08 10:12
1- 1	0	6428300.URPN.	USPAT	2003/05/08 10:13
-	29	("3505446" "3685784" "3991146"	USPAT	2003/05/08 10:13
		"4184835" "4464322" "4470786"	1	
1		"4618466" "4770833" "4954308"	1	
		"5049344" "5049526" "5110515"	1	
		"5174941" "5326243" "5344600"	1	
1		"5366368" "5429488" "5451153"	1	
		"5480296" "5523038" "5558883"	1	
		"5609889" "5626886" "5650177" "5714106" "5798070" "5989471"	1	
		"6030569" "6224360").PN.	1	
1. 1	26	5817545.URPN.	USPAT	2003/05/08 10:18
1-	20	6558982.URPN.	USPAT	2003/05/08 10:19
1 -	6	("5817545" "5874324" "5998243"	USPAT	2003/05/08 10:19

r -	36	("3930114" "4043027" "4437141"	USPAT	2003/05/08 10:23
	30	"4455274" "4460537" "4470786"	ODIAL	2003/03/00 10:23
	ì	"4688152" "4778641" "4823234"		
	1	"4859722" "4861251" "4868349"	İ	
	ì	"4890152" "4893172" "4935581"		
	1	"4954877" "4954878" "4961105"		
	ì	"4972253" "4975765" "5019673"		
	1	"5049526" "5093282" "5108955"		
1]	"5132778" "5136366" "5153385"		
	ĺ	"5191511" "5216278" "5218759"		
		"5241133" "5296738" "5328870"		
		"5355283" "5370517" "5395226").PN.		
-	40	5108955.URPN.	USPAT	2003/05/08 10:26
-	7	("4266239" "4541005" "4778641" "4822550" "4823234" "4868638"	USPAT	2003/05/08 10:43
		"4890152").PN.		
_	3	6081978.URPN.	USPAT	2003/05/08 12:10
_	1 3	("5336272" "6001671" "6033933").PN.	USPAT	2003/05/08 12:11
	113	((((mold near2 (upper lower)) and	USPAT;	2003/05/08 12:18
	1 ***	semiconductor and (chip die wafer)) and	US-PGPUB;	2003/03/00 12:12
1	1	(leadframe (lead nearl (inner outer))))	EPO; JPO;	1
		and (sealing sealed encapsulant	DERWENT	
	}	encapsulating encapsulated)) and (vent		
		vacuum)		
-	389176		USPAT;	2003/05/08 12:19
		and semiconductor and (chip die wafer))	US-PGPUB;	
1	1	and (leadframe (lead near) (inner	EPO; JPO;	
		outer)))) and (sealing sealed encapsulant	DERWENT	
1	}	encapsulating encapsulated)) and (method		
		process)) and ((die mounting) adj pad))		0000 (05 (00 10 10
-	91	(((((mold near2 (upper lower)) and	USPAT;	2003/05/08 12:19
		semiconductor and (chip die wafer)) and	US-PGPUB;	
1	}	(leadframe (lead nearl (inner outer)))) and (sealing sealed encapsulant	EPO; JPO; DERWENT	N .
		encapsulating encapsulated)) and (vent	DERWENT	1
	1	vacuum)) not ((((((mold near2 (upper		1
	l	lower)) and semiconductor and (chip die	Į.	1
	1	wafer)) and (leadframe (lead nearl (inner		
	ļ	outer)))) and (sealing sealed encapsulant		1
	ŀ	encapsulating encapsulated)) and (method		1
	ļ	process)) and ((die mounting) adj pad))		
-	25	5147821.URPN.	USPAT	2003/05/08 12:24
-	2	("4866506" ("4944908").PN.	USPAT	2003/05/08 12:26
-	25	5147821.URPN.	USPAT	2003/05/08 13:43
-	53	5474958.URPN.	USPAT	2003/05/08 13:44
-	4	5776800.URPN.	USPAT	2003/05/08 13:45
-	5	("5101324" "5130889" "5309026" "5394298" "5474958").PN.	USPAT	2003/05/08 13:45
	2	5874319.URPN.	USPAT	2003/05/08 13:48
-	21	5874319.0RPN. ("3777365" "3811182" "4881885"	USPAT	2003/05/08 13:48
-	21	"4932883" "5147821" "5173451"	OSFMI	2003/03/00 13.40
1	1	"5203401" "5237269" "5322207"		
	l	"5336649" "5367253" "5378981"		
		"5424652" "5459351" "5474958"		
	ł	"5475317" "5489538" "5548884"		
		"5568057" "5589781" "5591649").PN.		
_	2	("4866506" "4944908").PN.	USPAT	2003/05/08 13:53
-	2	("4866506" "4944908").PN.	USPAT	2003/05/08 13:53
-	5	"6081978"	USPAT;	2003/05/12 09:17
1			US-PGPUB;	
1	I		EPO; JPO;	
1	1		DERWENT	1
-	3	("5336272" "6001671" "6033933").PN.	USPAT	2003/05/12 08:46
-	740	(memory adj chip) near3 array	USPAT;	2003/05/12 09:36
			US-PGPUB;	
1	1		EPO; JPO;	1
			DERWENT	
-	471	((memory adj chip) near3 array) and	USPAT;	2003/05/12 09:18
1		semiconductor	US-PGPUB;	1
1	1		EPO; JPO; DERWENT	1

r=	137	((memory adj chip) near3 array) and	USPAT;	2003/05/12 09:20
	1	(semiconductor nearl (package device))	US-PGPUB;	
	1	• •	EPO; JPO;	
			DERWENT	
-	8	((memory adj chip) near3 array) with known	USPAT;	2003/05/12 09:37
	1		US-PGPUB;	
	1		EPO; JPO;	1
			DERWENT	
-	1406	(memory near chip) near4 array	USPAT;	2003/05/12 09:36
			US-PGPUB;	1
			EPO; JPO;	
	ł		DERWENT	1
-	15		USPAT;	2003/05/12 09:37
		known	US-PGPUB;	1
			EPO; JPO;	1
			DERWENT	1 .
-	7		USPAT;	2003/05/12 09:37
		known) not (((memory adj chip) near3	US-PGPUB;	1
		array) with known)	EPO; JPO;	1
	2102		DERWENT	1
-	2102		USPAT;	2003/05/19 08:33
		(chip die wafer)	US-PGPUB;	!
			EPO; JPO;	1
	1640	((tab near3 lead) and semiconductor and	DERWENT	2003/05/19 08:36
-	1640	(chip die wafer)) and (lead with	USPAT; US-PGPUB;	2003/05/19 08:36
	1	(electrode bump ball terminal pad))	EPO; JPO;	
	1	(electrode bump ball terminal pad))	DERWENT	1
_	123	(((tab near3 lead) and semiconductor and	USPAT:	2003/05/19 08:37
	123	(chip die wafer)) and (lead with	US-PGPUB;	2003/03/13 08:37
	1	(electrode bump ball terminal pad))) and	EPO; JPO;]
	1	(conductive nearl (vias (through ad)	DERWENT	1
		hole)))	DDILIII	1
_	94	((((tab near3 lead) and semiconductor and	USPAT;	2003/05/19 08:38
		(chip die wafer)) and (lead with	US-PGPUB;	
		(electrode bump ball terminal pad))) and	EPO; JPO;	1
	A.	(conductive nearl (vias (through adj	DERWENT	
		hole)))) and (seal sealed sealing		
		encapsulant encapsulated encapsulating)		1
-	43	((((tab near3 lead) and semiconductor and	USPAT;	2003/05/19 08:38
		(chip die wafer)) and (lead with	US-PGPUB;	1
		(electrode bump ball terminal pad))) and	EPO; JPO;	1
	1	(conductive nearl (vias (through adj	DERWENT	1
	1	hole)))) and (seal sealed sealing	Į.	Į.
	1	encapsulant encapsulated encapsulating))	1	1
		and (stacked stacking)	Į.	(